

### **General Clock Generator**

### PRODUCT DESCRIPTION

MS5351M is an I<sup>2</sup>C configurable, 3-channel output clock generator chip, which can completely replace crystals, crystal oscillators, phase-locked loops, and output buffers used in cost-sensitive applications. Thanks to the use of fractional frequency phase locked loop and high-precision fractional frequency divider structure, MS5351M can generate any clock output from 2.5kHz to 200MHz.

#### **FEATURES**

- Highly integrated analog circuit to demodulate and decode
- 3 channels output non-integer related clocks from 2.5kHz to 200MHz
- I<sup>2</sup>C user-defined configuration output clock
- Accurate frequency synthesis
- Low output jitter
- Can work with low-cost, fixed-frequency quartz crystals: 25MHz or 27MHz
- Output clock supports static phase shift
- Programmable control of output clock rise/fall time
- Glitch-free frequency switching
- Independent power supply pins Internal core circuit power supply VDD:

2.5V or 3.3V Output stage

- High internal power supply rejection ratio can save external filter capacitor
- Adjustable output delay
- Compatible with HCSL and PCIE Gen 1 applications

#### **APPLICATIONS**

- HD TV, DVD/Blu-ray, set-top box
- Audio/video equipment, Game consoles
- Printers, scanners, projectors
- Hand-held devices
- Home gateway equipment
- Network/communication
- Servers, storage
- Quartz crystal/crystal oscillator/phase-locked loop replacement

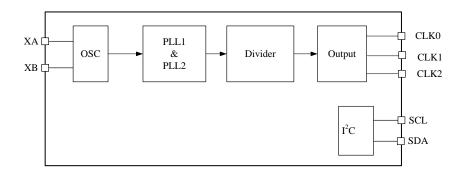
### PACKAGE/ORDERING INFORMATION

Part Number	Package	Marking
MS5351M	MSOP10	MS5351M



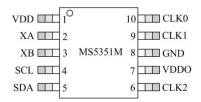


## SIMPLIFIED BLOCK DIAGRAM





## **PIN CONFIGURATIONS**



Pin	Symbol	Туре	Description
1	VDD	power	Internal circuit power supply
2	XA	input	External quartz crystal input
3	ХВ	input	External quartz crystal input
4	SCL	input	$\mbox{I}^2\mbox{C}$ clock input, at least $1\mbox{k}\Omega$ pull-up resistor must be connected
5	SDA	input/output	${ m I}^2{ m C}$ data input/output, at least 1k $\Omega$ pull-up resistor must be connected
6	CLK2	output	Output clock
7	VDDO	power	Output stage power supply
8	GND	ground	Reference GND
9	CLK1	output	Output clock
10	CLK0	output	Output clock



### **ABSOLUTE MAXIMUM RATINGS**

Note: It is not allowed to exceed the range of rated value in actual application. [1]

**Table 1. Limiting Condition**.

Parameter	Symbol	Condition	Rated value	Unit
Internal supply voltage	VDD		-0.5 to 3.8	V
Output stage supply voltage	VDDO		-0.5 to 3.8	V
Input pin voltage	VIN_SCL	SCL,SDA	-0.5 to 3.8	V
	VIN_XA/XB	XA,XB	-0.5 to 1.3	V
Junction temperature	TJ		-55 to 150	°C
Soldering iron temperature (lead-free) [2]	T <sub>PEAK</sub>		260	°C
Duration of soldering iron temperature at T <sub>PEAK</sub> (lead-free) [2]	T <sub>P</sub>		10	Second

<sup>[1]</sup> Exceeding the absolute rated maximum value may cause permanent damage to the chip

<sup>[2]</sup> The chip meets the JEDEC J-STD-020 specification



## **RECOMMEND OPERATING CONDITION**

## **Table 2.Operating Condition**

Symbol	Parameter	Min	Тур	Max	Unit
Operating temperature	T <sub>A</sub>	-40	25	105	°C
Internal circuit voltage	VDD	3.0	3.3	3.6	V
		2.25	2.5	2.75	V
		1.71	1.8	1.89	V
Output stage voltage	VDDO	2.25	2.5	2.75	V
		3.0	3.3	3.6	V



# **ELECTRICAL CHARACTERISTICS**

Table 3. Electrical characteristics (VCC=3.3V, TA =  $25^{\circ}$ C, unless otherw ise noted.)

Parameter	Symbol	racteristics (VCC=3.3V, TA = 25°C, un less	Min.	Typ.	Max.	Unit		
DC Characteristic		Condition	141111.	iyρ.	IVIUX.	Offic		
VDD Current	I <sub>DD</sub>	3 channel output		33		mA		
Single channel output	I <sub>DDOx</sub>	C <sub>1</sub> =5pF, Less than 100MHz		5		mA		
stage current	BBOX	Maximum drive capacity						
Input Current	I <sub>SCL</sub>	SCL,SDA			10	uA		
Output impedance	Z <sub>O</sub>	3.3V VDDO,High drive		50		Ω		
AC Characteristic								
Power-on time	T <sub>RDY</sub>	From VDDmin to effective output clock, f <sub>CLKn</sub> >1MHz		2	10	ms		
Power-on time when PLL bypass	Т <sub>вур</sub>	From VDDmin to effective output clock, f <sub>CLKn</sub> >1MHz		0.5	1	ms		
Output frequency switching time	T <sub>FREQ</sub>	f <sub>CLKn</sub> >1MHz			20	us		
Output phase shift	P <sub>STEP</sub>			333		ps/ste p		
Spread spectrum range	SS <sub>DEV</sub>	Down spread spectrum, 0.1% per step	-0.1		-2.5	%		
		Center spread spectrum, 0.1% per step	±0.1		±2.5	%		
Spread spectrum	SS <sub>MOD</sub>		30	31.5	33	kHz		
modulation rate								
Crystal specifications			25					
Quartz crystal frequency	f <sub>XTAL</sub>		25		27	MHz		
Load capacitance	C <sub>XL</sub>		6		12	pF		
Equivalent series resistance	r <sub>ESR</sub>				150	Ω		
Maximum drive level	d <sub>L</sub>		100			uW		
Input voltage	V <sub>IN_XA/AB</sub>	XA and XB	-0.3		1.1	V		
Output clock specificatio					ı			
Output frequency	F <sub>CLK</sub>		0.0025		200	MHz		
Load capacitance	C <sub>L</sub>				15	pF		
Duty cycle	DC	F <sub>CLK</sub> <160MHz	45	50	55	%		
		F <sub>CLK</sub> <160MHz	40	50	60	%		
Rise Time	t <sub>r</sub>	20%~80%,C <sub>L</sub> =5pFMaximum drive		0.5	1.2	ns		
Fall time	t <sub>f</sub>	20%~80%,C <sub>L</sub> =5pFMaximum drive		0.5	1.2	ns		
Output high level	V <sub>OH</sub>	C <sub>L</sub> =5pF	VDD- 0.6			V		





Output low level			V <sub>OL</sub>	C <sub>L</sub> =5pF					0.6	V
Period jitter	Period jitter J <sub>PER</sub>		$J_{PER}$	3 channels simultaneously output		output		60	180	ps,pk
Adjacent clock jitter			$J_{CC}$	3 channels si	multaneously	output		60	180	ps,pk
I <sup>2</sup> C Specification (SCL, SDA)										
Parameter	Sym	nbol Condition		n	Standard mode		Fast mode			Unit
					100	kbps		400k	bps	
					Min.	Max.	Min		Max.	V
Low-level input	V <sub>ILI2C</sub>				-0.5	0.3*V <sub>DDI2C</sub>	-0.5	5	0.3*V <sub>DDI2C</sub>	V
voltage										
High-level input	V <sub>IHI20</sub>	С			0.7*V <sub>DDI2C</sub>	3.6	0.7*V	DDI2C	3.6	V
voltage										
Schmidt hysteresis	V <sub>HYS</sub>				-	-	0.1		-	V
voltage										
Low-level output	V <sub>OLI2</sub>	:C	V <sub>OLI2C</sub> =2.	5/3.3V,	0	0.4	0		0.4	V
voltage			Open dr	ain, 3mA						
			current	sink						
Input Current	I <sub>II2C</sub>				-10	10	-10	)	10	uA
Pin capacitance	C <sub>I2C</sub>		VIN=-0.1	toV <sub>DDI2C</sub>	-	4	-		4	pF
I <sup>2</sup> CBus pause time	T <sub>TO</sub>		Pause er		25	35	25		35	ms

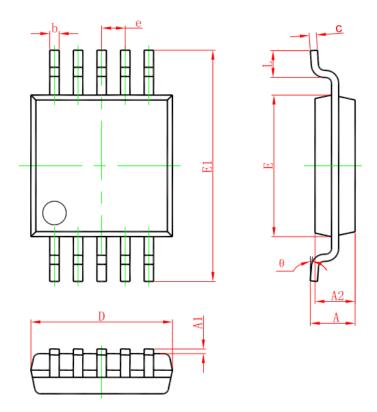
Version number: V1.1

#### NOTE:

- [1] Only 2 clocks larger than 112.5MHz are allowed to be output at the same time
- [2] The clock jitter test is 10000 cycles, and measured at the maximum output drive capacity
- [3] Jitter is highly dependent on frequency configuration
- [4] I<sup>2</sup>C only supports 2.25V to 3.6V power supply



# **PACKAGE OUTLINE DIMENSIONS**

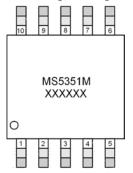


O. m.b. a. I	Dimensions In	Millimeters	Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0. 820	1. 100	0. 032	0. 043	
A1	0. 020	0. 150	0. 001	0.006	
A2	0. 750	0. 950	0. 030	0. 037	
b	0. 180	0. 280	0. 007	0. 011	
С	0. 090	0. 230	0. 004	0. 009	
D	2. 900	3. 100	0.114	0. 122	
е	0.50(	BSC)	0.020	(BSC)	
E	2. 900	3. 100	0. 114	0. 122	
E1	4. 750	5. 050	0. 187	0. 199	
L	0. 400	0.800	0. 016	0. 031	
θ	0°	6°	0°	6°	



## **Marking and Packaging Specifications**

1. Marking drawing description



MS5351M: Product name XXXXXX: Product code

2. Marking drawing pattern

Laser printing, contents in the middle, font type Arial.

3. Packaging Specifications

Device	Package	piece/reel	reel/box	piece /box	box/carton	piece/carton
MS5351M	MSOP10	3000	1	3000	8	24000

#### **REVISION HISTORY**

Revision	Revision Date	Description	Page
V1.0	2021.03.08	First Version	10
V1.1	2021.06.30	Add 3.3V supply voltage for VDDO of Table2 on page 5	10

### **STATEMENT**

- All Revision Rights of Datasheets Reserved for Ruimeng. Don't release additional notice.
   Customer should get latest version information and verify the integrity before placing order.
- When using Ruimeng products to design and produce, purchaser has the responsibility to observe safety standard and adopt corresponding precautions, in order to avoid personal injury and property loss caused by potential failure risk.
- The process of improving product is endless. And our company would sincerely provide more excellent product for customer.





MOS circuit operation precautions:

Static electricity can be generated in many places. The following precautions can be taken to effectively prevent the damage of MOS circuit caused by electrostatic discharge:

- 1. The operator shall ground through the anti-static wristband.
- 2. The equipment shell must be grounded.
- 3. The tools used in the assembly process must be grounded.
- 4. Must be used conductor packaging or antistatic materials packaging or transportation.

